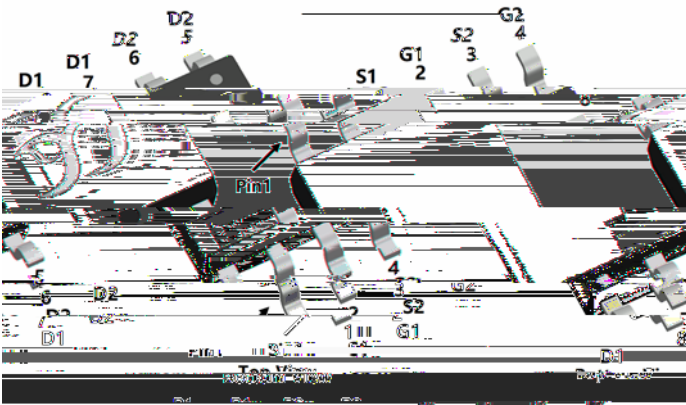
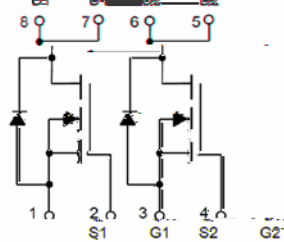




SOP-8



- V_{DS} 60V
- I_D 5.0A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 44mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) 49mohm
- Trench Power MV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free
- Battery protection
- Load switch
- Power management

($T_A=25$ unless otherwise noted)

Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25\% \text{ @ Steady State}$	I_D	5.0	A
	$T_A=70\% \text{ @ Steady State}$		4.0	
	$T_A=125\% \text{ @ Steady State}$		2.2	
Pulsed Drain Current ^A		I_{DM}	25	A
Total Power Dissipation @ $T_A=25\%$		P_D	3.1	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B		$R_{\theta JA}$	40.3	$^{\circ}C/W$
Avalanche energy ^C		EAS	30.25	mJ

Junction and Storage Temperature Range

T_J, T_{STG}

-55 +150

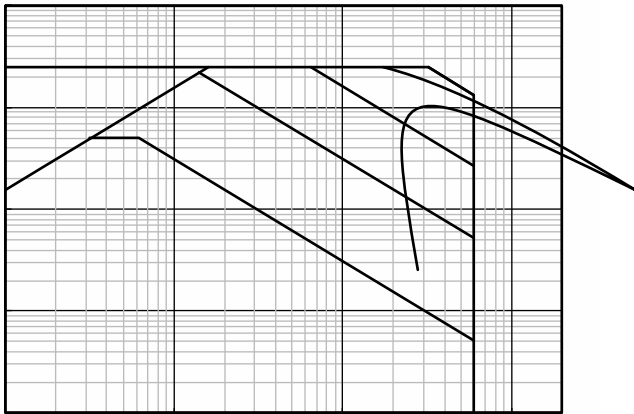
$\frac{3}{8}$ OUTER CARTON

					QUANTITY(pcs)	DELIVERY MODE
YJS05N06A	F2	Q05N06	4000	8000	64000	13" reel



■ (T_J=25 unless otherwise noted)

Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
		V _{DS} =60V, V _{GS} =0V, T _J =125℃			100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D				





SYMBOL	MIN.		
	0.053	0.069	
B	0.004	0.010	
		0.061	
D		0.020	
E			
F			
G	0.050BSC		1.270BSC
H			
J			
K			
	0°		



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